

# P8748H/P8749H 8048AH/8035AHL/8049AH/8039AHL/8050AH/8040AHL HMOS SINGLE-COMPONENT 8-BIT MICROCONTROLLER

- High Performance HMOS II
- Interval Time/Event Counter
- Two Single Level Interrupts
- Single 5-Volt Supply
- Over 96 instructions: 90% Single Byte
- Programmable ROMs Using 21V
- Easily Expandable Memory and I/O
- Up to 1.36 μs Instruction Cycle All Instructions 1 or 2 Cycles

The Intel MCS®-48 family are totally self-sufficient, 8-bit parallel computers fabricated on single silicon chips using Intel's advanced N-channel silicon gate HMOS process.

The family contains 27 I/O lines, an 8-bit timer/counter, and on-board oscillator/clock circuits. For systems that require extra capability, the family can be expanded using MCS®-80/MCS®-85 peripherals.

These microcontrollers are available in both masked ROM and ROMless versions as well as a new version, The Programmable ROM. The Programmable ROM provides the user with the capability of a masked ROM while providing the flexibility of a device that can be programmed at the time of requirement and to the desired data. Programmable ROM's allow the user to lower inventory levels while at the same time decreasing delay times and code risks.

These microcomputers are designed to be efficient controllers as well as arithmetic processors. They have extensive bit handling capability as well as facilities for both binary and BCD arithmetic. Efficient use of program memory results from an instruction set consisting of mostly single byte instructions and no instructions over 2 bytes in length.

Device	internal	Memory	RAM STANDBY
8050AH	4K x 8 ROM	256 x 8 RAM	yes
8049AH	2K x 8 ROM	128 x 8 FIAM	yes
8048AH	1K×8 ROM	64 x 8 RAM	yes
8040AHL	None	256 x 8 RAM	yes
8039AHL	None	128 x 8 RAM	yes
8035AHL	None	64 x 8 RAM	yes
P8749H	2K x 8 Programmable ROM	128 x 8 RAM	no
P8748H	1K x 8 Programmable ROM	64 x 8 RAM	no

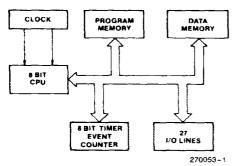
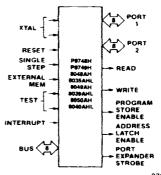


Figure 1. Block Diagram



270053-2

Figure 2. Logic Symbol

August 1989 Order Number: 270053-003

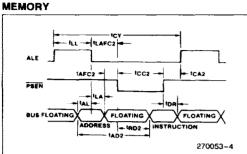
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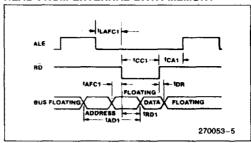


#### **WAVEFORMS**

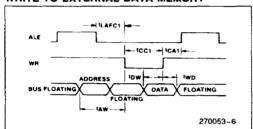
# INSTRUCTION FETCH FROM PROGRAM



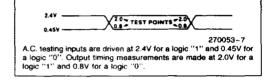
#### **READ FROM EXTERNAL DATA MEMORY**



#### WRITE TO EXTERNAL DATA MEMORY



## INPUT AND OUTPUT FOR A.C. TESTS



#### **PORT 1/PORT 2 TIMING**

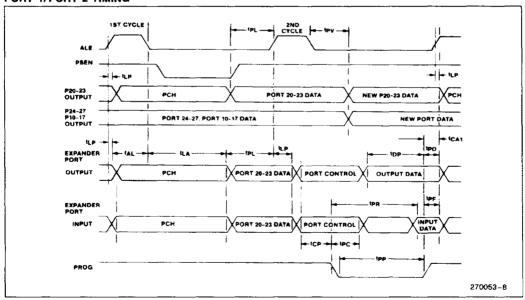




Table 1. Pin Description (Continued)

Symbol	Pin No.	Function	Device
T1	39	Input pin testable using the JT1, and JNT1 instructions. Can be designated the timer/counter input using the STRT CNT instruction.	All
INT	6	Interrupt input. Initiates an interrupt if interrupt is enabled. Interrupt is disabled after a reset. Also testable with conditional jump instruction. (Active low) interrupt must remain low for at least 3 machine cycles for proper operation.	All
RD	8	Output strobe activated during a BUS read. Can be used to enable data onto the bus from an external device.  Used as a read strobe to external data memory. (Active low)	All
RESET	4	Input which is used to initialize the processor. (Active low) (Non TTL $V_{\mathrm{IH}}$ )	All
		Used during power down.	8048AH 8035AHL 8049AH 8039AHL 8050AH 8040AHL
		Used during programming.	P8748H P8749H
		Used during ROM verification.	8048AH P8748H 8049AH P8749H 8050AH
WR	10	Output strobe during a bus write. (Active low) Used as write strobe to external data memory.	All
ALE	11	Address latch enable. This signal occurs once during each cycle and is useful as a clock output.  The negative edge of ALE strobes address into external data and program memory.	All
PSEN	9	Program store enable. This output occurs only during a fetch to external program memory. (Active low)	All
SS	5	Single step input can be used in conjunction with ALE to "single step" the processor through each instruction.	All
		(Active low) Used in sync mode.	8048AH 8035AHL 8049AH 8039AHL 8050AH 8040AHL
EA	7	External access input which forces all program memory fetches to reference external memory. Useful for emulation and debug. (Active high)	All
		Used during (18V) programming.	P8748H P8749H
		Used during ROM verification (12V).	8048AH 8049AH 8050AH
XTAL1	2	One side of crystal input for internal oscillator. Also input for external source. (Non TTL V <sub>IH</sub> )	Ali
XTAL2	3	Other side of crystal input.	All



# Table 2. Instruction Set

Accumulator			
Mnemonic	Description	Bytes	Cycles
ADD A, R	Add register to A	1	1
ADD A, @R	Add data memory to A	1	1
ADD A, #data	Add immediate to A	2	2
ADDC A, R	Add register with carry	1	1
ADDC A, @R	Add data memory with carry	1	. 1
ADDC A, #data	Add immediate with carry	2	2
ANL A, R	And register to A	1	1
ANLA, @R	And data memory to A	1	1
ANL A, #data	And immediate to A	2	2
ORL A, R	Or register to A	1	. 1
ORL A, @R	Or data memory to A	1	1
ORL A, #data	Or immediate to A	2	2
XRL A, R	Exclusive or register to A	1	1
XRL A, @R	Exclusive or data memory to A	1	1
XRL A, #data	Exclusive or immediate to A	2	2
INC A	Increment A	1	1
DEC A	Decrement A	1	1
CLR A	Clear A	1	1
CPL A	Complement A	1	1
DA A	Decimal adjust A	1	1
SWAP A	Swap nibbles of A	1	1
RLA	Rotate A left	1	1
RLC A	Rotate A left through carry	1	1
RR A	Rotate A right	1	1
RRC A	Rotate A right through carry	1	1

Input/Output			
Mnemonic	Description	Bytes	Cycles
IN A, P	Input port to A	1	2
OUTL P, A	Output A to port	1	2
ANL P, #data	And immediate to port	2	2
ORL P, #data	Or immediate to port	2	2
INS A, BUS	Input BUS to A	1	2
OUTL BUS, A	Output A to BUS	1	2
ANL BUS, #data	And immediate to BUS	2	2
ORL BUS, #data	Or immediate to BUS	2	2
MOVD A, P	Input expander port to A	1	2
MOVD P, A	Output A to expander port	1	2
ANLD P, A	And A to expander port	1	2
ORLD P, A	Or A to expander port	1	2

Registers			
Mnemonic	Description	Bytes	Cycles
INC R	Increment register	1	1
INC @R	Increment data memory	1	1
DEC R	Decrement register	1	1

Branch			
Mnemonic	Description	Bytes	Cycles
JMP addr	Jump unconditional	2	2
JMPP @A	Jump indirect	1	2
DJNZ R, addr	Decrement register and skip	2	2
JC addr	Jump on carry = 1	2	2
JNC addr	Jump on carry = 0	2	2
JZ addr	Jump on A zero	2	2
JNZ addr	Jump on A not zero	2	2
JT0 addr	Jump on $T0 = 1$	2	2
JNT0 addr	Jump on $T0 = 0$	2	2
JT1 addr	Jump on $T1 = 1$	2	2
JNT1 addr	Jump on $T1 = 0$	2	2
JF0 addr	Jump on $F0 = 1$	2	2
JF1 addr	Jump on $F1 = 1$	2	2
JTF addr	Jump on timer flag	2	2
JNI addr	Jump on $\overline{INT} = 0$	2	2
JBb addr	Jump on accumulator bit	2	2



Table 2. Instruction Set (Continued)

Subroutine			
Mnemonic	Description	Bytes	Cycles
CALL addr	Jump to subroutine	2	2
RET	Return	1	2
RETR	Return and restore status	1	2

Flags				
Mnemonic	Description	Bytes	Cycles	
CLRC	Clear carry	1	1	
CPLC	Complement carry	1	1	
CLR F0	Clear flag 0	1	1	
CPL F0	Complement flag 0	1	1	
CLR F1	Clear flag 1	1	1	
CPL F1	Complement flag 1	1	1	

Data Moves			
Mnemonic	Description	Bytes	Cycles
MOV A, R	Move register to A	1	1
MOV A, @R	Move data memory to A	1	1
MOV A, #data	Move immediate to A	2	2
MOV R, A	Move A to register	1	1
MOV @R, A	Move A to data memory	1	1
MOV R, # data	Move immediate to register	2	2
MOV @R, #data	Move immediate to data memory	2	2
MOV A, PSW	Move PSW to A	1	1
MOV PSW, A	Move A to PSW	1	1
XCH A, R	Exchange A and register	1	1
XCH A, @R	Exchange A and data memory	1	1
XCHD A, @R	Exchange nibble of A and data memory	1	1
MOVX A, @R	Move external data memory to A	1	2
MOVX @R, A	Move A to external data memory	1	2
MOVP A, @A	Move to A from current page	1	2
MOVP3 A, @A	Move to A from page 3	1	2

Timer/Counter				
Mnemonic	Description	Bytes	Cycles	
MOV A, T	Read timer/counter	1	1	
MOV T, A	Load timer/counter	1	1	
STRTT	Start timer	1	1	
STRT CNT	Start counter	1	1	
STOP TONT	Stop timer/counter	1	1	
EN TONTI	Enable timer/ counter interrupt	1	1	
DIS TONTI	Disable timer/ counter interrupt	1	1	

Control			
Mnemonic	Description	Bytes	Cycles
EN∔	Enable external interrupt	1	1
DIST	Disable external interrupt	1	1
SEL RBO	Select register bank 0	1	1
SEL RB1	Select register bank 1	1	1
SEL MB0	Select memory bank 0	1	1
SEL MB1	Select memory bank 1	1	1
ENTO CLK	Enable clock output on T0	1	1

Mnemonic	Description	Bytes	Cycles
NOP	No operation	1	1



#### **ABSOLUTE MAXIMUM RATINGS\***

Case Temperature Under Bias 0°C to +70°C
Storage Temperature65°C to +150°C
Voltage on any Pin with Respect
to Ground0.5V to +7V
Power Dissination 1 5W

NOTICE: This is a production data sheet. The specifications are subject to change without notice.

\*WARNING: Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "Operating Conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.

D.C. CHARACTERISTICS  $T_A = 0^{\circ}C$  to  $+70^{\circ}C$ ;  $V_{CC} = V_{DD} = 5V \pm 10\%$ ;  $V_{SS} = 0V$ 

Symbol	Parameter	Limits			Unit	Test Conditions	Device
		Min	Тур	Max	]	1 dat Conditions	24104
VIL	Input Low Voltage (All Except RESET, X1, X2)	-0.5		0.8	٧		All
V <sub>IL1</sub>	Input Low Voltage (RESET, X1, X2)	-0.5		0.6	٧		All
V <sub>IH</sub>	Input High Voltage (All Except XTAL1, XTAL2, RESET)	2.0		V <sub>CC</sub>	٧		All
V <sub>IH1</sub>	Input High Voltage (X1, X2, RESET)	3.8		V <sub>CC</sub>	٧		All
V <sub>OL</sub>	Output Low Voltage (BUS)			0.45	٧	I <sub>OL</sub> = 2.0 mA	Ail
V <sub>OL1</sub>	Output Low Voltage (RD, WR, PSEN, ALE)			0.45	V	I <sub>OL</sub> = 1.8 mA	All
V <sub>OL2</sub>	Output Low Voltage (PROG)			0.45	٧	I <sub>OL</sub> = 1.0 mA	All
V <sub>OL3</sub>	Output Low Voltage (All Other Outputs)			0.45	V	I <sub>OL</sub> = 1.6 mA	All
V <sub>OH</sub>	Output High Voltage (BUS)	2.4			V	I <sub>OH</sub> = -400 μA	All
V <sub>OH1</sub>	Output High Voltage (RD, WR, PSEN, ALE)	2.4			٧	I <sub>OH</sub> = -100 μA	All
V <sub>OH2</sub>	Output High Voltage (All Other Outputs)	2.4			٧	l <sub>OH</sub> = -40 μA	Ali



# **D.C. CHARACTERISTICS** $T_A = 0^{\circ}C$ to $+70^{\circ}C$ ; $V_{CC} = V_{DD} = 5V \pm 10\%$ ; $V_{SS} = 0V$ (Continued)

Symbol	Parameter	Limits			Unit	Test Conditions	Device	
		Min	Тур	Max	Oim	1 69t Conditions	Device	
IL1	Leakage Current (T1, INT)			±10	μА	V <sub>SS</sub> ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>	Ali	
I <sub>LI1</sub>	Input Leakage Current (P10-P17, P20-P27, EA, SS)			-500	μΑ	$V_{SS} + 0.45 \le V_{IN} \le V_{CC}$	Ali	
l <sub>L12</sub>	Input Leakage Current RESET	-10		-300	μА	V <sub>SS</sub> ≤ V <sub>IN</sub> ≤ 3.8	All	
lLO	Leakage Current (BUS, T0) (High Impedance State)			±10	μΑ	V <sub>SS</sub> ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>	All	
lDD	V <sub>DD</sub> Supply Current (RAM Standby)		3	5	mA		8048AH 8035AHL	
			4	7	mA		8049AH 8039AHL	
		·	5	10	mA	,	8050AH 8040AHL	
IDD +	Total Supply Current*		30	65	mA		8048AH 8035AHL	
			35	70	mA		8049AH 8039AHL	
			40	80	mA		8050AH 8040AHL	
			30	100	mA		P8748H	
			50	110	mA		P8749H	
V <sub>DD</sub>	RAM Standby Voltage	2.2		5.5	٧	Standby Mode Reset ≤V <sub>IL1</sub>	8048AH 8035AH	
		2.2		5.5	٧		8049AH 8039AH	
		2.2		5.5	٧		8050AH 8040AHL	
	1	1	1		ــــــــــــــــــــــــــــــــــــــ	<u> </u>	<u> </u>	

<sup>\*</sup>Icc + IDD are measured with all outputs in their high impedance state; FESET low; 11 MHz crystal applied; INT, SS, and EA floating.



# A.C. CHARACTERISTICS $T_A = 0$ °C to +70°C; $V_{CC} = V_{DD} = 5V \pm 10\%$ ; $V_{SS} = 0V$

Symbol	Parameter	f (t)	111	VHz	Unit	Conditions (Note 1)
		(Note 3)	Min	Max		
t	Clock Period	1/xtal freq	90.9	1000	ns	(Note 3)
t <sub>LL</sub>	ALE Pulse Width	3.5t-170	150		ns	
t <sub>AL</sub>	Addr Setup to ALE	2t-110	70		ns	(Note 2)
t <sub>LA</sub>	Addr Hold from ALE	t-40	50		ns	
t <sub>CC1</sub>	Control Pulse Width (RD, WR)	7.5t-200	480		ns	
t <sub>CC2</sub>	Control Pulse Width (PSEN)	6t-200	350		ns	
t <sub>DW</sub>	Data Setup before WR	6.5t-200	390		ns	
t <sub>WD</sub>	Data Hold after WR	t-50	40		ns	
t <sub>DR</sub>	Data Hold (RD, PSEN)	1.5t-30	0	110	ns	
t <sub>RD1</sub>	RD to Data in	6t-170		375	ns	
t <sub>RD2</sub>	PSEN to Data in	4.5t-170		240	ns	
t <sub>AW</sub>	Addr Setup to WR	5t-150	300		ns	
t <sub>AD1</sub>	Addr Setup to Data (RD)	10.5t-220		730	ns	
t <sub>AD2</sub>	Addr Setup to Data (PSEN)	7.5t-200		460	ns	
t <sub>AFC1</sub>	Addr Float to RD, WR	2t-40	140		ns	(Note 2)
t <sub>AFC2</sub>	Addr Float to PSEN	0.5t-40	10		ns	(Note 2)
tLAFC1	ALE to Control (RD, WR)	3t-75	200		ns	
tLAFC2	ALE to Control (PSEN)	1.5t-75	60		ns	
t <sub>CA1</sub>	Control to ALE (RD, WR, PROG)	t-65	25		ns	
t <sub>CA2</sub>	Control to ALE (PSEN)	4t-70	290		ns	
t <sub>CP</sub>	Port Control Setup to PROG	1.5t-80	50		ns	
tPC	Port Control Hold to PROG	4t-260	100		ns	
tpR	PROG to P2 Input Valid	8.5t-120		650	ns	
tpr	Input Data Hold from PROG	1.5t	0	140	ns	
top	Output Data Setup	6t-290	250		ns	
t <sub>PD</sub>	Output Data Hold	1.5t-90	40		ns	
tpp	PROG Pulse Width	10.5t-250	700		ns	
t <sub>PL</sub>	Port 2 I/O Setup to ALE	4t-200	160		ns	
t <sub>LP</sub>	Port 2 I/O Hold to ALE	0.5t-30	15		ns	
tpv	Port Output from ALE	4.5t + 100		5.0	ns	
toper	T0 Rep Rate	3t	270		ns	
t <sub>CY</sub>	Cycle Time	15t	1.36	15.0	μs	

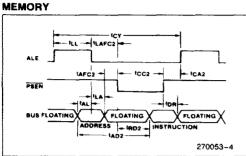
#### NOTES:

- 1. Control outputs:  $C_L = 80$  pF. BUS Outputs:  $C_L = 150$  pF. 2. BUS High Impedance Load 20 pF 3. f(t) assumes 50% duty cycle on X1, X2. Max clock period is for a 1 MHz crystal input.

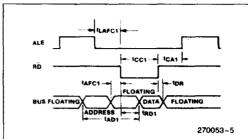


## **WAVEFORMS**

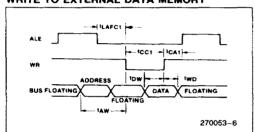
# INSTRUCTION FETCH FROM PROGRAM



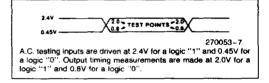
#### **READ FROM EXTERNAL DATA MEMORY**



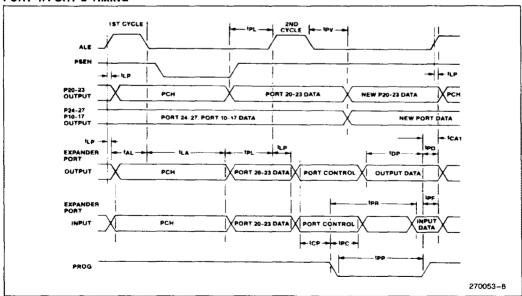
# WRITE TO EXTERNAL DATA MEMORY



#### INPUT AND OUTPUT FOR A.C. TESTS

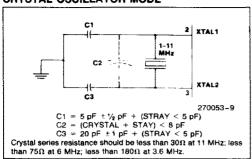


#### **PORT 1/PORT 2 TIMING**

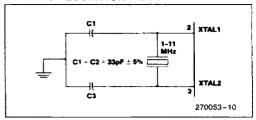




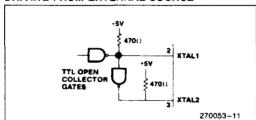
## CRYSTAL OSCILLATOR MODE



## **CERAMIC RESONATOR MODE**



## **DRIVING FROM EXTERNAL SOURCE**



270053-11 For XTAL1 and XTAL2 define "high" as voltages above 1.6V and "low" as voltages below 1.6V. The duty cycle requirements for externally driving XTAL1 and XTAL2 using the circuits shown above are as follows: XTAL1 must be high 35-65% of the period and XTAL2 must be high 35-65% of the period. Rise and fall times must be faster than 20 ns.



# PROGRAMMING AND VERIFYING THE P8749H/48H PROGRAMMABLE ROM

# **Programming Verification**

In brief, the programming process consists of: activating the program mode, applying an address, latching the address, applying data, and applying a programming pulse. Each word is programmed completely before moving on to the next and is followed by a verification step. The following is a list of the pins used for programming and a description of their functions:

Pin	Function
XTAL1	Clock Input (3 to 4.0 MHz)
XTAL2	
RESET	Initialization and Address Latching
TO	Selection of Program or Verifying Mode
EA	Activation of Program/Verify Modes
BUS	Address and Data Input
	Data Output During Verify
P20-P22	Address Input
V <sub>DD</sub>	Programming Power Supply
PROG	Program Pulse Input

#### **WARNING:**

An attempt to program a missocketed P8749H/48H will result in severe damage to the part. An indication of a properly socketed part is the appearance of the ALE clock output. The lack of this clock may be used to disable the programmer.

#### The Program/Verify sequence is:

- V<sub>DD</sub> = 5V, Clock applied or internal oscillator operating, RESET = 0V, T0 = 5V, EA = 5V, BUS and PROG floating. P10 and P11 must be tied to ground.
- 2. Insert P8749H/48H in programming socket
- 3. T0 = 0V (select program mode)
- 4. EA = 18V (activate program mode)
- 5. Address applied to BUS and P20-22
- 6. RESET = 5V (latch address)
- 7. Data applied to BUS
- 8. V<sub>DD</sub> = 21V (programming power)
- 9. PROG = V<sub>CC</sub> or float followed by one 50 ms pulse to 18V
- 10.  $V_{DD} = 5V$
- 11. T0 = 5V (verify mode)
- 12. Read and verify data on BUS
- 13. T0 = 0V
- 14. RESET = 0V and repeat from step 5
- Programmer should be at conditions of step 1 when P8749H/48H is removed from socket.

#### NOTE:

Once programmed the P8749H/48H cannot be erased.



# A.C. TIMING SPECIFICATION FOR PROGRAMMING P8748H/P8749H ONLY

 $T_A = 25^{\circ}C \pm 5^{\circ}C; V_{CC} = 5V \pm 5\%; V_{DD} = 21 \pm 0.5V$ 

Symbol	Parameter	Min	Max	Unit	Test Conditions
t <sub>AW</sub>	Address Setup Time to RESET	4t <sub>CY</sub>			
twa .	Address Hold Time After RESET	4t <sub>CY</sub>			
t <sub>DW</sub>	Data in Setup Time to PROG	4t <sub>CY</sub>			
t <sub>WD</sub>	Data in Hold Time After PROG	4t <sub>CY</sub>			
t <sub>PH</sub>	RESET Hold Time to Verify	4t <sub>CY</sub>			
tvppw	V <sub>DD</sub> Hold Time Before PROG	0	1.0	ms	,
typpH	V <sub>DD</sub> Hold Time After PROG	0	1.0	ms	
tpw	Program Pulse Width	50	60	ms	
t <sub>TW</sub>	T0 Setup Time for Program Mode	4t <sub>CY</sub>			
twr	T0 Hold Time After Program Mode	4t <sub>CY</sub>			
t <sub>DO</sub>	T0 to Data Out Delay		4t <sub>CY</sub>		
tww	RESET Pulse Width to Latch Address	4t <sub>CY</sub>			
t <sub>r</sub> , t <sub>f</sub>	V <sub>DD</sub> and PROG Rise and Fall Times	0.5	100	μs	
tcy	CPU Operation Cycle Time	3.75	5	μs	
t <sub>RE</sub>	RESET Setup Time before EA	4t <sub>CY</sub>			

#### NOTE

If Test 0 is high, t<sub>DO</sub> can be triggered by RESET.

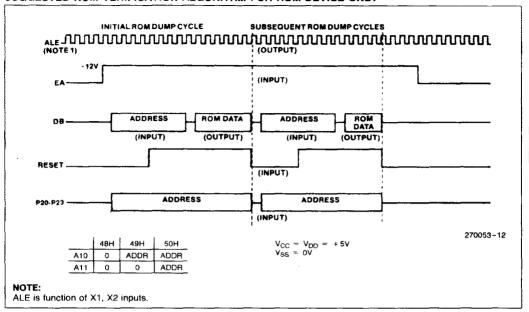
# D.C. CHARACTERISTICS FOR PROGRAMMING P8748H/P8749H ONLY

 $T_A = 25^{\circ}C \pm 5^{\circ}C; V_{CC} = 5V \pm 5\%; V_{DD} = 21 \pm 0.5V$ 

Symbol	Parameter	Min	Max	Unit	Test Conditions
V <sub>DDH</sub>	V <sub>DD</sub> Program Voltage High Level	20.5	21.5	V	
V <sub>DDL</sub>	V <sub>DD</sub> Voltage Low Level	4.75	5.25	٧	
V <sub>PH</sub>	PROG Program Voltage High Level	17.5	18.5	٧	
V <sub>PL</sub>	PROG Voltage Low Level	4.0	Vcc	٧	
VEAH	EA Program or Verify Voltage High Level	17.5	18.5	٧	
מסי	V <sub>DD</sub> High Voltage Supply Current		20.0	mA	
PROG	PROG High Voltage Supply Current		1.0	mA	
<sup>l</sup> EA	EA High Voltage Supply Current		1.0	mA	



#### SUGGESTED ROM VERIFICATION ALGORITHM FOR ROM DEVICE ONLY



# COMBINATION PROGRAM/VERIFY MODE (PROGRAMMABLE ROMS ONLY)

